

SKMD 202E, SKND 202E



SEMIPACK[®] 2

Ultrafast Epitaxial Diode Modules

SKND 202E

SKMD 202E

Features

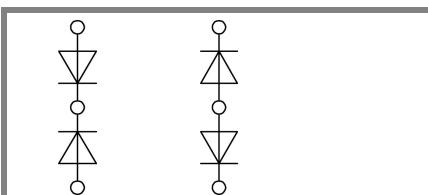
- Isolated metal baseplate
- Very short recovery times
- Low switching losses
- Up to 400 V peak inverse voltage
- SKMD common cathode
SKND common anode
- UL recognized, file no. E 63 532

Typical Applications

- Switched mode power converters
- Inverse diode for transistors in AC and DC motor controls
- Uninterruptible power supplies (UPS)

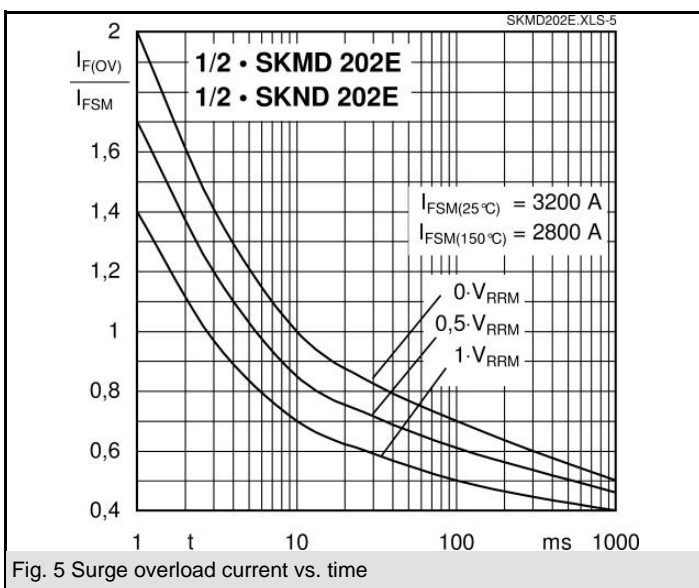
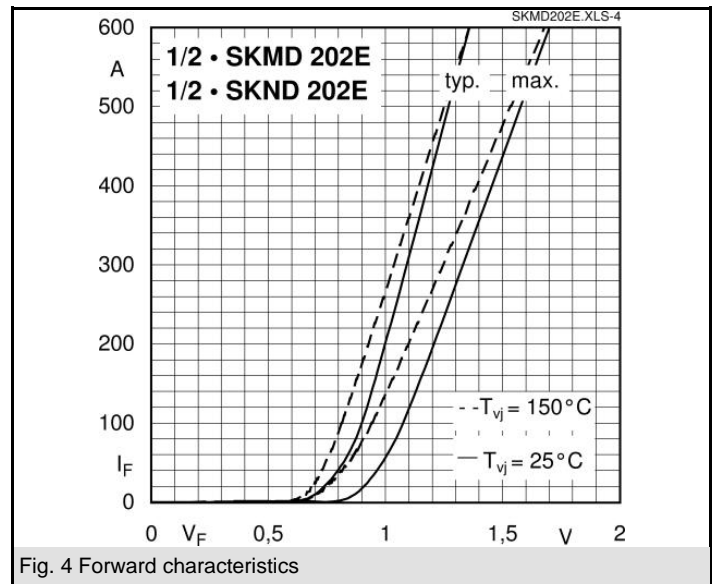
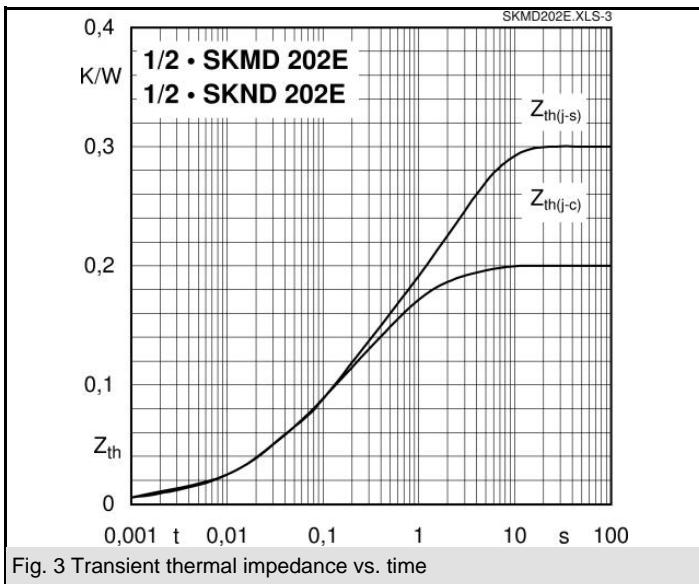
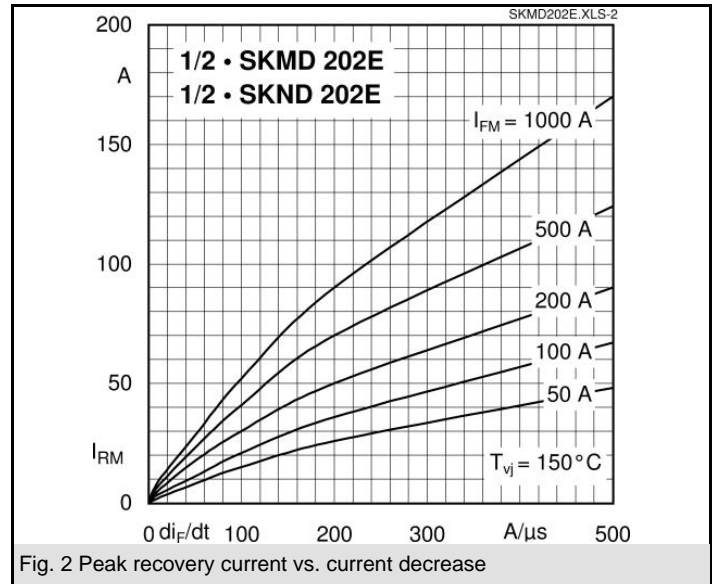
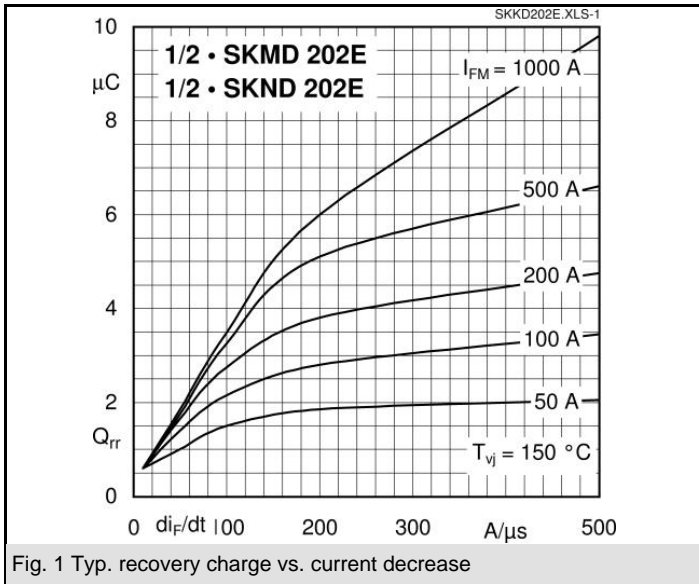
V_{RSM} V	V_{RRM} V	$I_{FRMS} = 325$ A (maximum value for continuous operation) $I_{FAV} = 202$ A (sin. 180, 50 Hz; $T_c = 87$ °C)	
200	200	SKMD 202E02	SKND 202E02
300	300	SKMD 202E03	SKND 202E03

Symbol	Conditions	Values	Units
I_{FAV}	sin. 180; $T_c = 85$ (100) °C	208 (156)	A
I_{FSM}	$T_{vj} = 25$ °C; 10 ms $T_{vj} = 150$ °C; 10 ms	3200 2800	A A
i^2t	$T_{vj} = 25$ °C; 8,3 ... 10 ms $T_{vj} = 150$ °C; 8,3 ... 10 ms	51000 39000	A ² s A ² s
V_F	$T_{vj} = 25$ °C; $I_F = 500$ A	max. 1,65	V
$V_{(TO)}$	$T_{vj} = 150$ °C	max. 0,8	V
r_T	$T_{vj} = 150$ °C	max. 1,5	mΩ
I_{RD}	$T_{vj} = 25$ °C; $V_{RD} = V_{RRM}$	max. 2	mA
I_{RD}	$T_{vj} = 130$ °C; $V_{RD} = V_{RRM}$	max. 100	mA
Q_{rr}	$T_{vj} = 150$ °C, $I_F = 50$ A,	2	μC
I_{RM}	$-di/dt = 100$ A/μs, $V_R = 100$ V	16	A
t_{rr}		-	ns
E_{rr}		-	mJ
$R_{th(j-c)}$	per diode / per module	0,2 / 0,1	K/W
$R_{th(c-s)}$	per diode / per module	0,1 / 0,05	K/W
T_{vj}		- 40 ... + 150	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3000 / 2500	V~
M_s	to heatsink	5 ± 15 %	Nm
M_t	to terminals	5 ± 15 %	Nm
a		5 * 9,81	m/s ²
m	approx.	250	g
Case	SKMD SKND	A 51 A 52	

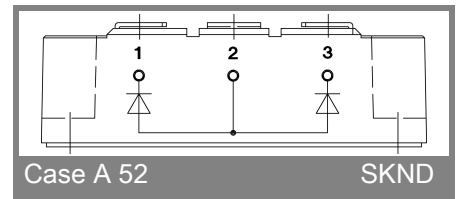
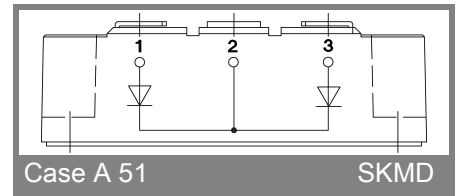
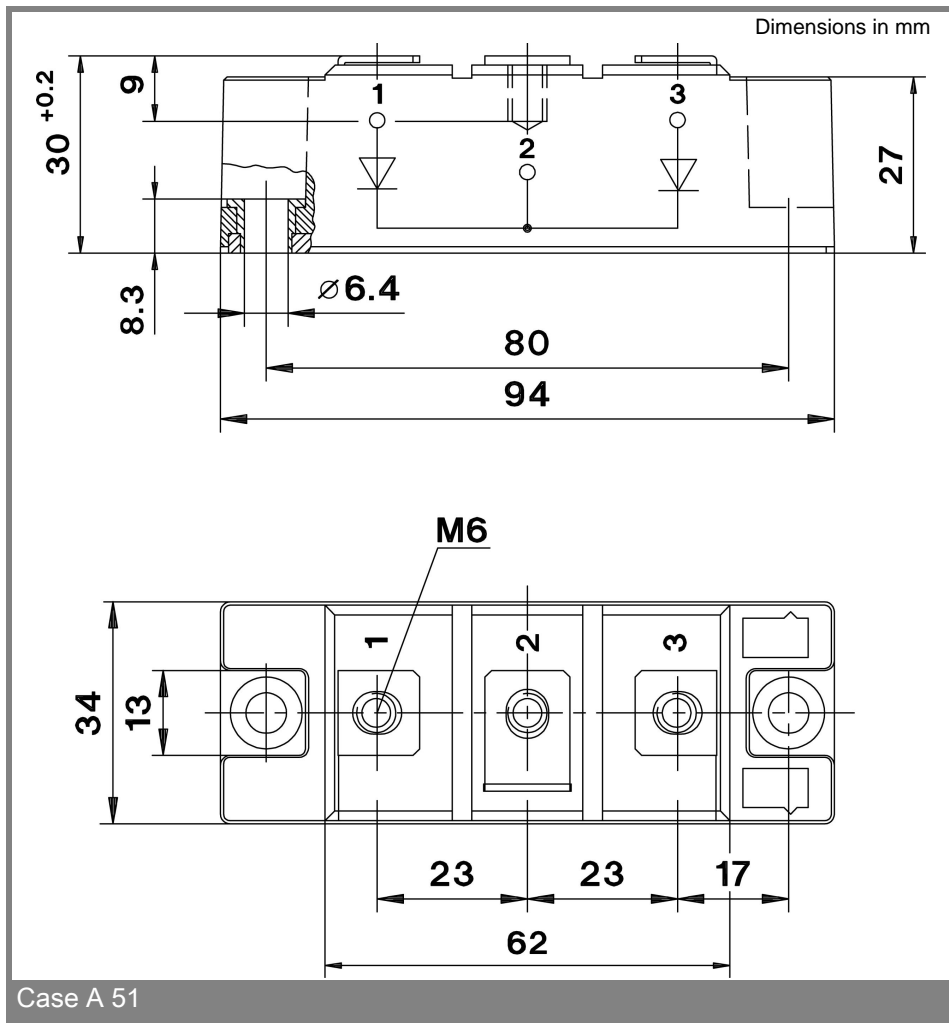


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